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Microwave Device

Microwave circuits are composed of various microwave devices. According to their functions, microwave devices can be divided into filters, circulators, isolators, switches, limiters, phase shifters, amplifiers, attenuators, detectors, mixers, frequency multipliers, frequency dividers, oscillators, frequency synthesizers, power amplifiers, couplers, etc. These devices can be used to easily build various microwave components and systems.

In today's pursuit of equipment miniaturization, most microwave devices have been made into MMIC. MMIIC has the advantages of small size, light weight, and stable performance, but it is difficult to integrate high-power and high-Q value circuits. Therefore, in the pursuit of high power or optimal performance of microwave front-end circuits, the use of discrete devices such as resistors, capacitors, inductors, diodes, triodes, and microwave transmission lines, connectors, and shielded shells to build microwave device modules still has a wide range of applications.

Our company has the ability to develop various microwave devices, especially in the development of the following types of devices, and has rich engineering experience.

- (1) Power Amplifier
- (2) Low Noise Amplifier
- (3) Microwave Switch
- (4) Limiter
- (5) Phase Shifter
- (6) Frequency Synthesizer
- (7) Filter

ZDTECH

Power Amplifier

Features:

(1) Using solid-state power devices such as LDMOS, GaAs, and GaN, the company can customize and develop pulse or continuous wave power amplifiers with a frequency coverage of 0.2MHz~40GHz and a power of 1W~1000W for users.

(2) The power amplifier can add power-on timing protection, output mismatch protection, over-temperature/over-voltage/over-current protection, over-excitation protection and other functions as needed, which can cope with various accidents and has strong anti-burning ability.

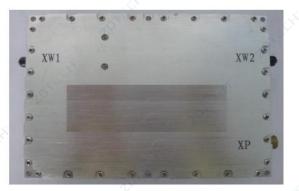
(3) It has excellent and mature pulse modulation technology, and can use RF signal modulation, gate or drain power supply modulation technology to realize amplifier pulse operation. The pulse rise and fall edges are less than 100nS, and the pulse top drop is <0.5dB.

(4) It has excellent external matching circuit design capabilities, which can give full play to the performance of the power amplifier tube and obtain the best power output capability or the best power conversion efficiency. The efficiency of the external matching GaN narrowband power amplifier module can reach more than 60%. The broadband matching of the amplifier can be achieved through transformers, transmission line impedance converters and other technologies, and it can be competent for the development of ultra-wideband amplifiers with operating frequencies spanning multiple octaves.

(5) Master excellent linearization technology, use power back-off, doherty, and analog pre-distortion technologies, and be competent for most communication power amplifier development.

(6) Master good thermal simulation skills, familiar with various heat dissipation designs such as natural heat dissipation, air cooling, and liquid cooling, master microstrip, stripline, and waveguide power synthesis technology, and be competent for high-power amplifier development.

C-Band Pulse Power Amplifier



GaN external matching amplifier High-speed power supply pulse debugging Power-on and power-off timing protection

_	
69	Working Frequency
<	Port Standing Wave
2	Small Signal Power Gain
4	Gain Fluctuation
2	P-1dB
1	Working Power Supply
S	Input/Output Connector
<	Appearance Size

3.8~4.3GHz	
≤1.5	ALC: NO
≥40dB	12
≤1dB	1. Starten and the starten and
≥38dBm	101 ET
±12V	10
SMA-50K	
≤150×110×35mm	

Ka-Band Pulse Power Amplifier

GaN power tube amplifier Rectangular waveguide power synthesis High-speed pulse power supply drain modulation Power-on/off timing protection

Working Frequen	су
Rising Ed	ge
Falling Ed	ge
Top Dr	op
Inter-Pulse Spurious Suppression	on
Saturated Output Pow	er
Power Supp	oly
Efficien	су
Power Interfa	ce
RF Input and Output Interfa	ce
Si	ze
Weig	ht

30-40GHz		
≤50ns		
50ns	1 ¹	
≤0.5dB	12	
≥60dBc	, A	
≥46.0dBm (duty cycle ≤20%, pulse v	width ≤20us);	
DC (+28V, -5V)	1V.	
about 30% (typical value)		
J30J-9-ZKP		
BJ320	12	
60X30X20mm	\$	
≤200g		

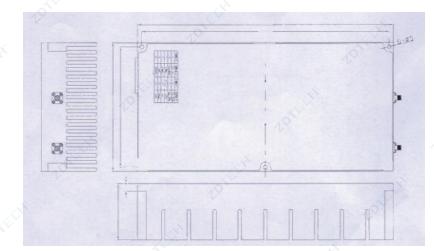
Ka Band-Pulse 100W Power Amplifier



Gan power tube internal matching amplifier Rectangular waveguide power synthesis High-speed pulse power supply drain modulation Power-on/power-off timing protection function

	Working Frequency
<u>_</u>	Rising Edge
<u>``</u>	Falling Edge
	Top Drop
Inte	r-Pulse Spurious Suppression
	Saturated Output Power
	Power Supply
J.K.	Efficiency
1011	Power Interface
R	F Input and Output Interface
	Size
	Weight

34-36GHz	
≤100ns	L.
≤100ns	12
≤0.5dB	,S
≥60dBc	OTEL
≥52.0dBm (duty cycle ≤20%,	pulse width ≤20us);
DC (+28V, -5V)	, clix
About 30% (typical value)	
J30J-31-ZKP	1
BJ320	2
110X90X20mm	J. L. L.
<1000g	10



S-Band 100W Power Amplifier

Continuous wave GaN power tube external matching amplifier 3dB bridge power synthesis

Power-on/power-off timing protection function

Over-temperature, mismatch, over-excitation protection function

Working Frequency 1dB Compression Point Output Power Falling Edge Output Flatness Small Signal Gain Power Supply

L.
10.
.s.
Shirt .
1×

6-18GHz Power Amplifier

6-18GHz Power Amplifier



Supports pulse and continuous wave working systems Single power supply, convenient system integration Power amplifier temperature detection, over-temperature protection Output power detection, mismatch protection

Working Frequency	6-18GHz
Output Saturation Power	≥44dBm
Power Gain	≥40dB
Power Supply	DC +28V

4dBm 0dB +28V

Narrowband Low Noise Amplifier

Low noise amplifiers with operating frequency relative bandwidth less than or equal to 20% are defined as narrowband low noise amplifiers. With the best noise matching technology, the product noise factor can reach the domestic advanced level. Products with higher performance and medium power can be customized.

C-Band Low Noise Amplifier



Working Frequency	
Noise Figure	
Port Standing Wave	19
Small Signal Power Gain	
P-1dB	
Working Power Supply	*
Input/Output Connector	
Appearance Size	

	. *
3.8~4.3GHz	1 th
≤1.2dB	1011
≤1.5	s ⁶
≥25±1.5dB	×
≥10dBm	de la companya de la comp
+5V	12
SMA-50K	15
≤87×40×16mm	OTE

Waveband	Relative	Noise Figure	Power Gain	P-1dB	Gain Flatness	VSWR
OTEL	Bandwidth	(dB)	(dB)	(dBm)	(±dB)	(max)
VHF	≤20%	0.7~2	≥20	10~20	0.5	≤1.5
Р	≤20%	0.5~2	≥20 √	10~20	0.5	≤1.5
L	≤20%	0.6~2	≥15	10~20	0.5	≤1.5
S	≤20%	0.7~2	≥15	10~20	0.5	≤1.8
C L	≤20%	1.2~2.5	≥10	5~15	0.5	≤1.8
X	≤20%	1.8~3	≥10	5~15	0.5	≤1.8
Ku	≤20%	2~4	≥10	5~15	0.5	≤2.0
		•			•	

Broadband Low Noise Amplifier

A low noise amplifier with an operating frequency relative to the bandwidth greater than or equal to 20% is defined as a broadband low noise amplifier. The amplifier adopts the best noise matching and takes into account the gain fluctuation index within the band. It has the characteristics of low noise figure and small gain fluctuation. Products with higher performance and medium power can be customized.

X-Band Low Noise Amplifier

	Working Frequency	5
	Noise Figure	
	Port Standing Wave	1
J ^X	Small Signal Power Gain	2
	Gain Fluctuation	1
	P-1dB	2
	Working Power Supply	_
	Input/Output Connector	5
	Appearance Size	<

5~10GHz	
≤2.2dB	12
≤2	, LIN
≥15dB	1911
≤2dB	12
≥10dBm	\$
+ 5V	
SMA-50K	19
≤25×25×8mm	

			r		i	
Waveband	Relative	Noise Figure	Power Gain	P-1dB	Gain Flatness	VSWR
	Bandwidth	(dB)	(dB)	(dBm)	(±dB)	(max)
VHF	≥20%	<2	≥20	10~17	≤1.5 1	≤2.5
Р	≥20%	<2	≥20	10~17	≤1.5	≤2.5
L	≥20%	<2	≥15	10~17	≤1.5	≤2.5
S	≥20%	<2	≥15	10~13	≤1.5	≤2.5
С	≥20%	<3	≥10	5~13	≤1.5	≤2.5
Х	≥20%	<4	≥10	5~13	≤1.5	≤2.5
Ku	≤20%	2~4	≥10	5~15	0.5	≤2.0

Microwave PIN Switch

Features:

(1) Bandwidth: The frequency can cover $0.01 \sim 18$ GHz;

(2) High power: The pulse power can reach several kilowatts, and the continuous wave power can reach hundreds of watts;

(3) Fast switching speed: The typical value of the switching speed is tens of nanoseconds;

(4) High isolation: The isolation of the switch using special technology can reach more than 100dB.

(5) Good performance: It has excellent performance such as low insertion loss and low standing wave ratio.

(6) Small size: The glass bead interface is used to achieve surface mount installation.

(7) High reliability: It adopts advanced processes such as chip eutectic, metal sealing structure, exquisite appearance and reliable quality.

2~8GHz Microwave Switch



Working Frequency
Insertion Loss
Switching Time
Port Standing Wave
Power Handling
Drive Voltage
Isolation
In-Band Flatness
Operating Temperature
Dimension

2GHz~8GHz≤1.5dB <50ns ≤1.5 ≥27dBm +5V, -12V (Negative pressure, current ≤500mA) ≥30dBc ±0.5dB 40°C~+70°C

75×52×10mm

Limiter

Features:

(1) Bandwidth: frequency can cover 0.02~18GHz;

(2) High power: pulse power can reach several kilowatts, continuous wave power can reach hundreds of watts;

(3) Good performance: has excellent performance such as low insertion loss and low standing wave ratio.

(4) Small size: glass bead interface is adopted, which can realize surface mount installation.

(5) High reliability: advanced processes such as chip eutectic are adopted, metal sealing structure, exquisite appearance and reliable quality.

S-Band High-Power Limiter



Working Frequence
Insertion Los
Port Standing Wav

Withstand Power

Leakage Power Operating Temperature

Dimension

2GHz~4GHz	
≤0.8dB	Ż.
≤1.5	STEL.
continuous wave ≥50)dBm
10% duty cycle pulse	≥60dBm
≤20dBm	19 ¹⁶
-40℃~+70℃	

20×12×18mm

Phase Shifter

Features:

(1) Bandwidth: The frequency can cover 0.02~18GHz;

(2) High power: The pulse power can reach hundreds of watts, and the continuous wave power can reach tens of watts;

(3) High speed: The typical value of phase switching time is tens of nanoseconds;

(4) High precision: The phase shift accuracy is high, which can reach $\pm 1^{\circ}$ within the working frequency band;

(5) High stability: The phase stability is good and is not affected by factors such as stability and signal level.

(6) Good performance: It has excellent performance such as low insertion loss and low standing wave ratio.

(7) Small size: It can be packaged in a small size with a glass bead interface;

(8) High reliability: It adopts advanced processes such as chip eutectic, metal sealing structure, exquisite appearance and reliable quality.

Six-Bit Non-Dispersive Phase Shifter

	Left.	The second se	
	Working Frequency	5.2GHz~5.8GHz	
	Phase Shift Step	5.625°	
_	Insertion Loss	≤6dB	
	Amplitude Fluctuation	≤1dB	4
Y.	Input/Output VSWR	≤1.5	other .
	Phase Shift Accuracy	≤2.5°	V
	Power Handling	≥1W	
	Phase Switching Time	≤150ns	
_	Power Supply and Control	±5V, TTL level	
	Operating Temperature	-40℃~+70℃	L.
	Dimension	96×38×12mm	101
_			

Integer-Division Basic Loop Frequency Synthesizer

Use an integer-division PLL frequency synthesis chip with a low phase noise floor to achieve frequency synthesis with a single loop. The product circuit is simple and small in size, but still has high comprehensive indicators. The circuit can be designed according to user requirements to meet special requirements. When the requirements for spurious suppression are relaxed and special circuit measures are taken, the frequency hopping time can be made shorter.

Wave	Relative	Phase Noise(Mid	Power	Spur	Step Size	Harmonic
band	Bandwidth	Frequency)dBc/	Output	Suppression	(Hz)	Suppression
10		Hz@1kHz	(dBm)	(dBc)		(dBc)
Р	≤100%	100	(0~20)±1	>70	10k~50M	20~50
L	≤100%	90	(0~15)±1	>70	10k~50M	20~50
S	≤80%	85	(0~15)±1	>70	10k~50M	20~50
С	≤40%	80	(0~10)±1	>65	10k~50M	20~50
x	≤12%	75	(0~10)±1	>60	10k~50M	20~50
Ku 🔨	≤7%	70	(0~10)±1	>60	10k~50M	20~50

Fractional Frequency Basic Ring Synthesizer

The biggest advantage of FN-PLL technology is that it can still obtain a very fine step length when using a higher phase detection frequency fp, thereby improving the phase noise index. However, the existence of its inherent fractional spurious makes the spurious suppression index poor. With the continuous development of fractional spurious suppression technology, especially the maturity of Z- \triangle modulation technology, this problem has been solved to a large extent. The company uses advanced FN-PLL chips with low phase noise floor and 12bit/22bit modulus to design this type of product, and its step length can reach the Hz level.

Wave	Relative	Phase	Spur	Step	Settling	Harmonic	Output
band	Bandwidth	Noise(dBc/	Suppression	Size	Time	Suppression	Power
Š.		Hz@1kHz)	(dBc)	(Hz)	(µs)	(dBc)	(dBm)
Р	≤100%	115	60~75	10~50M	20~200	20~50	0~20
L	≤100%	105	60~75	10~50M	20~200	20~50	0~15
S	≤80%	100	60~75	10~50M	20~200	20~50	0~15
С	≤40%	95	60~75	10~50M	20~200	20~50	0~10
x	≤12%	90	60~75	10~50M	20~200	20~50	0~10
Ku	≤7%	85	60~75	10~50M	20~200	20~50	0~10

Fractional-Number Mixing Loop Phase-Locked Frequency Synthesizer

On the basis of using M/N loop to reduce PLL phase noise, when the step size is fine, the FN-PLL chip is used to increase the phase detection frequency, which can further reduce the frequency deterioration of loop phase noise, thereby improving the phase noise index.

Wave	Relative	Phase Noise	Spur	Step Size 🔨	Settling	Harmonic	Power
band	Bandwidth	(dBc/	suppression	(Hz)	Time(µs)	Suppression	Output
		Hz@1kHz)	(dBc)	1511		(dBc)	(dBm)
L	≤25%	-115	50~75	10Hz~30MHz	50~200	20~50	0~10
S	≤25%	-115	50~75	10Hz~30MHz	50~200	20~50	0~10
ŚC	≤25%	-110	50~75	10Hz~30MHz	50~200	20~50	0~10
Х	≤25%	-105	50~75	10Hz~30MHz	50~200	20~50	0~10
Ku	≤25%	-100	50~75	10Hz~30MHz	50~200	20~50	0~10
Ku	≤7%	85	60~75	10~50M	20~200	20~50	0~10
	L S C X Ku	band Bandwidth L $\leq 25\%$ S $\leq 25\%$ C $\leq 25\%$ X $\leq 25\%$ Ku $\leq 25\%$	band Bandwidth (dBc/ L $\leq 25\%$ -115 S $\leq 25\%$ -115 C $\leq 25\%$ -110 X $\leq 25\%$ -105 Ku $\leq 25\%$ -100	band Bandwidth (dBc/ suppression $Hz@1kHz$) (dBc) L $\leq 25\%$ -115 $50^{\sim}75$ S $\leq 25\%$ -115 $50^{\sim}75$ C $\leq 25\%$ -110 $50^{\sim}75$ X $\leq 25\%$ -105 $50^{\sim}75$ Ku $\leq 25\%$ -100 $50^{\sim}75$	band Bandwidth (dBc/ Hz@1kHz) suppression (dBc) (Hz) L $\leq 25\%$ -115 50^{-75} $10Hz^{-3}0MHz$ S $\leq 25\%$ -115 50^{-75} $10Hz^{-3}0MHz$ C $\leq 25\%$ -110 50^{-75} $10Hz^{-3}0MHz$ X $\leq 25\%$ -105 50^{-75} $10Hz^{-3}0MHz$ Ku $\leq 25\%$ -100 50^{-75} $10Hz^{-3}0MHz$	band Bandwidth (dBc/ suppression (Hz) Time(μ s) L $\leq 25\%$ -115 $50^{\circ}75$ $10Hz^{\circ}30MHz$ $50^{\circ}200$ S $\leq 25\%$ -115 $50^{\circ}75$ $10Hz^{\circ}30MHz$ $50^{\circ}200$ C $\leq 25\%$ -110 $50^{\circ}75$ $10Hz^{\circ}30MHz$ $50^{\circ}200$ X $\leq 25\%$ -110 $50^{\circ}75$ $10Hz^{\circ}30MHz$ $50^{\circ}200$ Ku $\leq 25\%$ -105 $50^{\circ}75$ $10Hz^{\circ}30MHz$ $50^{\circ}200$	band Bandwidth (dBc/ suppression (Hz) Time(μ s) Suppression L $\leq 25\%$ -115 $50^{\circ}75$ $10Hz^{\circ}30MHz$ $50^{\circ}200$ $20^{\circ}50$ S $\leq 25\%$ -115 $50^{\circ}75$ $10Hz^{\circ}30MHz$ $50^{\circ}200$ $20^{\circ}50$ C $\leq 25\%$ -110 $50^{\circ}75$ $10Hz^{\circ}30MHz$ $50^{\circ}200$ $20^{\circ}50$ X $\leq 25\%$ -110 $50^{\circ}75$ $10Hz^{\circ}30MHz$ $50^{\circ}200$ $20^{\circ}50$ Ku $\leq 25\%$ -105 $50^{\circ}75$ $10Hz^{\circ}30MHz$ $50^{\circ}200$ $20^{\circ}50$ Ku $\leq 25\%$ -100 $50^{\circ}75$ $10Hz^{\circ}30MHz$ $50^{\circ}200$ $20^{\circ}50$

Direct Digital Frequency Synthesizer

DDS realizes frequency synthesis based on the new digital waveform synthesis technology. With the development of semiconductor technology, the clock of DDS can reach 12GHz, which can generate 40% of the clock frequency output and the frequency reaches 3GHz.

The phase noise floor of DDS chip is also continuously reduced, and the spurious-free dynamic range index (SFDR) is getting higher and higher, which greatly improves its practicality. The biggest advantages of DDS are fine step length, agile frequency change and low phase noise.

		Phase Noise	10	Spur			Settling	Harmonic
Frequency	Relative	(dBc/	S	uppressio	on	Step Size	Time	Suppression
Output	Bandwidth	Hz@1kHz)	±50	±1	±5	(Hz)	(µs)	(dBc)
\$		10	(KHz)	(MHz)	(MHz)			, Š
DC~3000	100%	<-115	85	80	78	<1	<1	<50
MHz		×		J.				ΓV.

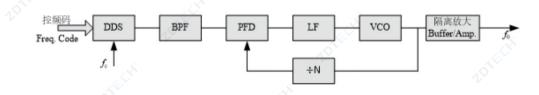
(1) Spurious suppression is related to the output frequency. The above spurious indicators are the values when using a 1GHz clock and 100MHz output;

(2) DDS frequency hopping time is mainly determined by the external frequency code processing circuit. When there are few frequency hopping points, using the inherent frequency register of DDS, the frequency hopping time can be less than 50ns;

③ When the DDS used has a high noise floor, it will affect the phase noise indicator of the output frequency.

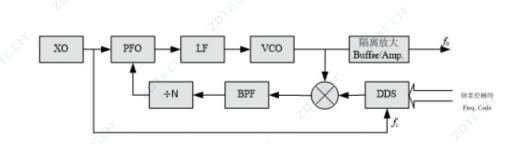
DDS Plus PLL Frequency Synthesizer

Technical Solution 1



When using DDS as the reference source of PLL, the maximum output frequency of DDS is limited by the allowed clock frequency. Combining DDS with PLL can overcome this shortcoming and generate a fine-step frequency source that can cover the entire microwave frequency band. It has excellent performance of high resolution and wide bandwidth, but in the high microwave band, due to the large N value, the spurious in-band deterioration of DDS is large.

					Spur Suppression
Waveband	Relative	Phase Noise (dBc/	Step	Settling	(dBc)
10	Bandwidth	Hz@1kHz)	Size(Hz)	Time(µs)	±10kHz
J ^K L	DC~fout	-105	1	50~200	75
S	DC~fout	-95	1	50~200	70
С	DC~fout	-90	1,4	50~200	65
х	DC~fout	-85	1	50~200	60
Ku	DC~fout	-80	1	50~200	55



Technical Solution 2

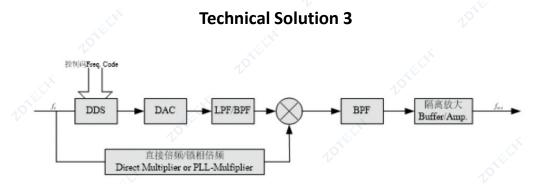
The PLL interpolation DDS form is adopted, which has the excellent performance of high resolution and no deterioration of DDS spurious. When N is a fixed value, only DDS frequency hopping can achieve faster frequency hopping. The change of N value can achieve broadband output.

Waveband	Relative	Phase Noise	Step Size	Settling Time	Spur Suppression (dBc)
	Bandwidth	(dBc/Hz@10kHz)	(Hz)	(µs)	±10kHz
L	40%	-110	1	50~200	75
S 10	15%	-100	1	50~200	75
, C	8%	-98	1	50~200	75
x	5%	-95	1	50~200	70
Ku	3%	-85	1	50~200	70

(1) Output power, power supply and power consumption, and operating temperature can be produced according to user requirements;

(2) If the DDS+frequency multiplication scheme is adopted, its indicators are similar to the DDS
 Plus PLL frequency synthesizer technical scheme 1;

(3) When the user provides an external reference source (or clock), the requirements for phase noise indicators must be guaranteed to achieve the listed frequency synthesis phase noise indicators.



This solution uses out-of-loop mixing to achieve the output of Technical Solution 2. In addition to the characteristics of high resolution and low phase noise, as long as the frequency-multiplied output is a single-point frequency, the frequency hopping time is determined only by DDS, thus achieving agile frequency switching.

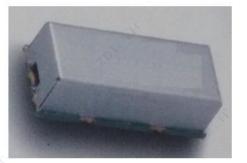
Waveband	Relative Bandwidth	Phase Noise(dBc/ Hz@10kHz)	Step Size(Hz)	Settling Time(µs)	Spur Suppression (dBc)
L	40%	-120	101	<1	50
S	15%	-110	1	<1	50
c 🔗	8%	-105	1	<1	50
X	4.6%	-100	1	<1	50
Ku	2.8%	-95	1	<1	50

When the output frequency range is reduced, the spurious suppression index can be higher than the parameters in the above table.

LC Filter

The circuit simulation and parameter optimization are performed by dedicated CAD software. The operating frequency can cover 2~5000MHz, with low insertion loss, good passband standing wave characteristics and high out-of-band attenuation.

70MHz Bandpass Filter



Center Frequency	70MHz
1dB Bandwidth	10MHz
Insertion Loss	≤2.5dB
f0±20MHz Out-of-Band Suppression	≥60dB
Input/Output Impedance	50Ω
Dimension	30×12×8mm

2500MHz Bandpass Filter



-			
	Center Frequency	2500MHz	
	1dB Bandwidth	300MHz	
	Insertion Loss	≤2dB	
	f0±20MHz Out-of-Band Suppression	≥50dB	
	Input/Output Impedance	50Ω	
J.	Input/Output VSWR	≤1.5	j,
	Dimension	30×12×8mm	

Microstrip Filter

Microstrip filters are classified into low-pass, high-pass, band-pass and band-stop filters according to frequency selection functions. For LPF, the technical solutions of high and low impedance lines and suspended microstrips are adopted; for BPF, the technical solutions of parallel coupling lines, branch lines, tapped comb lines, tapped interdigital lines, suspended microstrips, SIR and cross-coupling by SIR are adopted; for HPF, the technical solutions of branch lines and suspended microstrips are adopted. It has many advantages such as small size, light weight and wide frequency band.



C-Band Microband Filter

	Center Frequency
10	1dB bandwidth
S ^K	Insertion Loss
f0±800MHz Out-	of-Band suppression
Input	t/Output impedance
	Input/Output VSWR
10	Dimension

1.2		
5000MHz	1012	
600MHz	A.	
≤2.5dB	19 ^{fc}	
≥40dB	V	
50Ω		
≤1.8	DIEL	
100×50mm		

Cavity Filter

Frequency covers 500MHz~18GHz, with low insertion loss, good passband standing wave characteristics and high out-of-band attenuation. The cavity filters provided by our company are in three forms: comb filter, interdigital filter and coaxial resonant cavity filter. The input and output methods are standard SMA connectors or detachable connectors, and a variety of flexible lead pin forms can also be used as needed.

C-Band Bandpass Filter



E.	Center Frequency	4000MHz	LOTE
_	3dB Bandwidth	15MHz	2
_	f0±3MHz In-Band Fluctuation	≤0.5dB	Ś.
_	Insertion Loss	≤4dB	
	f0±60MHz Out-of-Band Suppression	≥75dB	
2	Input/Output Impedance	50Ω	ALL D
10	Input/Output VSWR	≤1.3	T.
_	Dimension	140×32X33mm	11th

Multiplex /Duplex Filter

A duplex/multiplex filter (also known as a frequency divider) is another common filter besides a switch filter. It consists of two or more filters that share a common input port and can separate signals into different frequency bands.

S-Band Duplex Filter



ter 1 Operating Frequency f1	
Filter 2 Center Frequency f2	
Inband Insertion Loss	,
Input/Output VSWR	
Isolation between F1 and F2	

2100MHz±50MHz 2400MHz±50MHz ≤1.5dB ≤1.3

≥80dB

Microwave Component

Microwave components are products assembled from various microwave components and other parts. They also include RF circuits, power circuits, control circuits, and embedded software. According to their main functions, they can be divided into frequency synthesis components, frequency conversion components, switch filtering components, and receiving and transmitting components.

1. Frequency synthesis components are used to generate various frequencies and provide clock signals, local oscillator signals, calibration signals, etc. for the entire system. Phase noise, frequency hopping time, clutter suppression, frequency and power stability are key indicators of frequency synthesis components. We can customize and develop various high-stability frequency synthesis components with low phase noise, low clutter, and agile frequency conversion.

2. The core of the frequency conversion component is the mixer, amplification, and filtering, which are used to realize the frequency conversion from RF to IF or IF to RF of the entire machine, and can integrate clock and local oscillator signals. How to plan the frequency, filter out the mixing clutter, and improve the anti-interference ability is the difficulty of the frequency converter design. We can customize and develop various wide-band, large dynamic, and low-spurious frequency conversion components.

3. The switch filter component consists of a filter and a multi-way switch. It can select a certain frequency band signal and block other frequency signals according to work requirements. It has a wide range of applications in broadband microwave systems. We can develop various switch filter components for customization, which have the advantages of small size and high out-of-band suppression.

4. The receiving and transmitting components are usually composed of RF filters, duplexers, limiters, low noise amplifiers, attenuators, phase shifters, power amplifiers and other front-end circuits for receiving and transmitting. With the antenna, the RF signal can be received or transmitted. At the same time, switches, intermediate frequency filters, frequency converters, frequency synthesizers, etc. can be integrated to form a complete receiving and transmitting link.

Frequency Synthesizer Component

Features:

(1) With the function of converting intermediate frequency signal to X band; including reference clock source; Can output the 1GHz reference clock signal;

(2) It has the X-band correction signal generation function, and the correction signal output can be closed;

(3) It has the frequency point control and status query function

· · · · · ·		
Medium Freq. Input	Frequency	170MHz±15MHz
A CONTRACTOR OF THE OWNER OWNER OF THE OWNER OWNE	Level	5±2dBm
RF Output	Frequency	10.52GHz±150MHz
	Frequency Hopping Step	5MHz
	Amplitude	5dBm±2dBm
	Phase Noise	≤-107dBc/Hz@1kHz
	Spurious Suppression	≤-65dBc
Correction Signal Output	Frequency	10.52GHz±150MHz
	Frequency Hopping Step	100kHz
	Amplitude	-30dBm±3dBm
20TECT:	Output Phase Noise	≤-95dBc/Hz@1kHz
	Output Spurious	≤-50dBc
1GHz Ref. Clock Output	Level	5±2dBm
	Phase Noise	≤-135dBc/Hz@1kHz
10 ^{11C}	Spurious	≤-65dBc(Out-of-band)
100MHz Sampling Clock	Level	5±2dBm
	Spurious	≤-80dBc
	Frequency Stability	≤1ppm/year
	Frequency Accuracy	≤1ppm
	Phase Noise	≤-155dBc/Hz@1kHz
	Power Supply	+12V, 2A
1.	Control	RS485
ż.	V	ALC: NOT

XL Frequency Source Component

Frequency Conversion Component

Features:

- (1) VPX plate structure, broadband super heterodyne secondary frequency conversion;
- (2) With the hopping frequency local vibration and clock, can be automatically synchronized with

the external clock

VPX Architecture RF Component

	A Contractor of the second
Input Frequency	0.95~3.8GHz
Output Frequency	140MHz
Gain	30±2dB
Gain Step	1dB
Gain Flatness	1.5dB
Third-order Cutoff Point	≥30dBm
Signal Bandwidth	72MHz
Signal 1dB Bandwidth	±20/±40MHz
Noise Figure	≤12dB(full-gain test)
Frequency Step Interval	10kHz
Phase Noise	
	≤-80dBc/Hz@1kHz
	≤-90dBc/Hz@10kHz
10	<-100dBc/Hz@100kHz
Image Rejection	≥70dBc
Clutter Signal	≥60dBc
Input/Output VSWR	<1.5
LO Leakage	Input end is less than -70dBm
Output P-1	≥±15dBm
Operating Temperature	-25~+70℃
Storage Temperature	-40~+80 ℃
Input/Output Interface	SMA-К
Supply Voltage	±5.5V, +12V
Control Mode	VPX Interface
Dimension	Standard 6 UVPX Card
Weight	<1kg
Dimension	Standard 1U case
External Ref.	10MHz, internal and external clock switching

Switch Filter Component

Feature:

(1) The switch filter is mainly composed of the filter set, the multi-channel selection switch and the control circuit.

(2) It has the advantages of small size, fast frequency switching speed, and high out-of-band inhibition.

C-band 5-in Switch Filter



A.	Center Frequency
OTEL	1dB Bandwidth
	Insertion Loss
±100MHz Out-or	f-band Suppression
	Port VSWR
Third	l-order Cutoff Point
Frequen	cy Switching Speed
1 CONTRACTOR	Appearance Size
19	

<u>F1、F2、F3、F4、F</u>	5	1011	
20MHz			
≤5dB	1 ¹		
≥60dB	101		
≤1.5			
≥30dBm		. Ś.	
≤200nS		TEL	
160*100*30 (mm)		12	

Transmitter

Features:

(1) All-solid-state transmitter, with up-conversion function, built-in local oscillator; High-speed pulse power supply drain modulation;

(2) Power management function, convenient for users to adjust output power; Power amplifier unit temperature detection, providing early warning and alarm indication;

(3) Single power supply is convenient to use, power supply with slow start protection function;Output mismatch protection function; Output power real-time detection function.

Ku-band Transmitter



72	IF-FRE
15	RF
≥7(Spurious Suppression
≥5(LO Suppression
≥7(Sideband Suppression
≤1	Rising Edge
<u>≤1</u>	Falling Edge
≤0.	Top Drop
≥5	Saturation Output Power
DC	Power Supply
Ab	Efficiency
130	Power Interface
BJ1	RF Interface
SN	LO/IF Interface
≤4.	Weight
24	Dimension

720MHz	
15-17GHz	12
≥70dBc	W.
≥50dBc	, d ⁵
≥70dBc	10 ¹¹
≤100ns	
≤100ns	a la
≤0.8dB	10
≥55.0dBm (Duty cycle	e ≤30%, pulse width ≤300us)
DC(+24V~+30V)	ž.
About 20%	and the second se
J30J-31-ZKP	12
BJ180	d ⁱ
SMA-K	ACTE.
≤4.4Kg	V
240*200*60 (mm)	

Transceiver Component

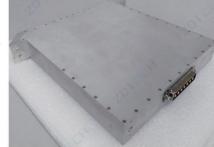
Feature:

(1) The component contains 2 receiving channels, 1 receiving and transmitting channel, and 1 self-test channel;

(2) It has transmission power detection; transmission channel temperature detection;

(3) It has transmission port mismatch protection function; transmission power management; the receiving port has a limiting function;

(4) It has a built-in power supply component, single power supply, and is easy to use.



Transmitting **IF-FRE** 720MHz Channel RF 14-18GHz **Spurious Suppression** ≥70dBc ≥50dBc LO Suppression Sideband Suppression ≥70dBc **Rising Edge** ≤100ns Falling Edge ≤100ns ≤0.8dB **Top Drop** ≥55.0dBm (Duty cycle ≤30%, pulse **Saturation Output Power** width ≤300us) annel

ReceivingCh

Noise Figure	4dB (C
Overall Gain	≥30dB
Gain Flatness	±0.5 dE
Spurious Suppression	≥40dB
Image Rejection	≥45dB
Channel Isolation	≥50dB
Channel Amplitude Imbalance	≤±0.5d
Channel Relative Phase	≤±10°
Channel Phase Variation with	≤±10°
Temperature	

B (Channel), 3dB (Receiving channe	l)
OdB	
5 dB/50MHz	
0dBc	
5dBc	
OdBc	
0.5dB	
10°	

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Ku-Band Transceiver Component

	Isolation Between Transmitting	≥60dBc	
	Channel and Receiving Channel	V	
	Power Supply	DC(+10V)	
	Efficiency	About 20%	
	Power Interface	J30J-31-ZKP	
	RF/IF Interface	SMA-К	
	Weight	≤2Kg	
	Dimension	248*230*30 (mm)	

Features:

- (1) Adopt high-speed gate pulse modulation technology;
- (2) Have output power detection function;
- (3) Have power amplifier temperature detection function;
- (4) Have power supply timing protection function;
- (5) Have self-check function for transmitting branch and receiving branch;
- (6) Can carry out wave control communication through RS485 serial port to complete the phase

shift of transmitting and receiving branch.

L-band Transceiver Component



Transmitting	Working Frequency	0.96-1.25GHz
Channel	Input Excitation Level	+10dBm~+15dBm
	Saturation Output Power	≥55.0dBm (Duty cycle ≤12%, pulse
		width ≤30us)
	Rising Edge	≤100ns
	Falling Edge	≤100ns
	Тор Drop	≤0.8dB
	Spurious Suppression	≥70dBc
12	Phase Shift No.	6
X	Phase Shift Accuracy	<u>≤±5°</u>
pi ^{ter}	Power Supply	DC(+50V,+28V,+12V,+5V,-5V)
	Efficiency	About 60%
Receiving	Noise Figure	4dB (Channel), 3dB (Receiving channel
Channel	Gain	≥20dB
	In-band fluctuation	≤1dB
	CNC Attenuation	5 bits, step in 0.5dB
	Anti-burning power	≥500W
	Port VSW	≤1.5
	Transmit/receive Switching Time	≤500ns
	Transmit and Receive Isolation	≥20dB
	Power Interface	J35H29-01
	RF/IF Interface	ВМА-К
	Weight	≤1.5Kg
12	Dimension	300×147×30 (mm)

Receiver Component

Feature:

(1) CPCI board structure, ultra-wideband double-conversion superheterodyne receiving components;

(2) It has the advantages of low noise, high sensitivity, and large dynamic range;

CPCI Architecture Ultra-Wideband Receiver Component



12	and all an a set	
Input Frequency	30~3000MHz	
Output Frequency	76.8/70MHz	
Gain	30±2dB	1
Gain Step	1dB	
Gain Flatness	≤2dB	
Output Third-Order Intercept Point	≥40dBm	
Input Second-Order Intercept Point	≥45dBm	
Output Third-Order Intercept Point	≥10dBm	
Signal Bandwidth	20 MHz (narrow band 500 kHz)	
Noise Figure	≤10dB	
Phase Noise	≤-100dBc/Hz@10kHz	
	≤-120dBc/Hz@100kHz	
Medium Freq. Suppression	≥90dBc	
Image Rejection	≥90dBc	
Spurious Signal	≤-110dBm	
Input/Output VSWR	≤2.0	
LO Leakage	≤-90dBm	3
Frequency Synthesis Step Interval	10kHz	6
Operating Temperature	-25~+70℃	
Storage Temperature	-40~+80°C	
Output P-1	≥±15dBm	
Input Interface	SMA-K	
Output Interface	SMA-K	
Control Mode	CPCI Interface	
Dimension	Standard 6 UCP CI Card	V
Power Supply Voltage	±5.5V,+12V	
External Ref.	10MHz, internal and external clock switching	5

Microwave Equipment

Microwave equipment is a product assembled from various microwave components, microwave functional components and other parts. It has a good human-computer interaction interface, comes with a battery or can work directly with AC power, meets certain specific functions, and can be used independently. We can develop various microwave equipment according to user requirements and have rich engineering experience in the development of portable signal sources, switch matrices and devices.

1. Portable signal sources are small in size, light in weight, low in power consumption, come with batteries, have most of the functions of general signal sources, and have excellent performance indicators. They are very suitable for carrying and can meet the needs of field use.

2. The switch matrix has multiple inputs and multi-channel interfaces, and can connect any input to any output. According to the connection requirements of input and output, it can be divided into one-input and one-output, multiple-input and one-output, one-input and multiple-output, and multiple-input and multiple-output. The switch matrix has the advantages of wide working frequency band, flat gain in the band, large power capacity, high isolation, and fast switching speed. It is widely used in multi-channel radar and communication systems or multi-channel test systems.

3. The frequency converter equipment is usually made into a standard chassis, powered by 220V mains electricity; it has a keyboard and display screen, and can manually configure the working parameters; it uses network port and serial port communication, can configure the working parameters, and has the function of indicating the working status. The inverter equipment we developed has the advantages of wide working frequency band, flat gain in the band, small output noise, strong anti-interference ability, high linearity, and large dynamic range. It has a wide range of applications in measurement and control systems.

Portable Signal Source(customized)

Features:

- (1) Built-in rechargeable battery, convenient for field testing and maintenance;
- (2) Built-in control keyboard and display screen, supports manual control;

Output signal has wide frequency band, low phase noise, large dynamic range, and high (a)tter suppression.

100MHz~3GHz Portable Signal Source



	Working Frequency
	Frequency Resolution
	Frequency Stability
	Frequency Conversion
Full	-frequency Output Power Range
	Power Percision
	Harmonic Suppression
	Clutter Suppression
	Built-in battery for continuous
	working hours

100MHz~3GHz		
0.1MHz	101	5
≤1×10-6/24h		10
≤50ms		×.
-60dBm~+12dBm		ALL C
≤±1.0dB		17
≥20dBc	1 ¹	
≥50dBc	DIFE	
≥8h		

Switch Matrix

Features:

(1) The equipment adopts modular design, can be disassembled and assembled repeatedly and ensure technical indicators.

(2) It uses Gigabit network to communicate with the host computer to realize remote control of the switch matrix.

(3) It has the advantages of wide working frequency bandwidth, high isolation, good channel consistency and long service life.

1~2.5GHz 5x13 Switch Matrix

	Working Frequency
	Input Power
Chanr	nel Switch Isolation (Off) Degree
	Interpass Isolation
	Insertion Loss
	Channel Delay Repeatability
	Channel-Phase Repeatability
1014	Channel Consistency
V	Switching Response Speed
	VSWR
	Impedance
	Working Life

1GHz~2.5GHz	ji ji
≥20dBm	10
≥90dBc (when input=0dBm)
≥90dBc (when input=0dBm	
≤10dB	12
≤ 1ns	di seconda
<u>≤3°</u>	Ster.
≤1dB	1 ¹
≤0.1s	
≤2.0	
50Ω	10
500 Thousand times	

L Band Downconversion Equipment

L-Band 950-2150MHz Downconversion Equipment

Input Frequency
Output Frequency
Gain
Gain Step
Gain Flatness
Third-Order Intermodulation
Output P-1
Signal 1dB Bandwidth
Noise Figure
Frequency Step Interval
Frequency Stability
Input Signal Level
Phase Noise

	Harmonic Suppression
Spuriou	s Suppression (max. gain)
AL N	Aedium Freq. Suppression
10	Image Rejection
	Input/Output VSWR
	Group Delay
	LO Leakage
	Operating Temperature
	Storage Temperature
LOTT	Input Interface
	Output Interface
	Local Control
	Remote Control
	Dimension
	External Ref.
	External Kel.

	O``
950-2150MHz	· V
70/140MHz	J. J.K.
30dB	
0.1dB step controllable	
≤1dBp-p	2
≤-60dBc	Letter .
≥10dBm	10
±20/±40MHz	
≤12dB	ALEL
10kHz	17
-80~-20dBm	,d
≤-85dBc/Hz@100Hz	1010
≤-100dBc/Hz@1kHz	
≤-105dBc/Hz@10kHz	
≤-110dBc/Hz@100kHz	
≥45dBc	
≥45dBc	
≥60dBc	<u></u>
≥70dBc	T.
<1.5	S.
<1ns	10 ¹
Input end is less than -70dBm	
- 10~+55 ℃	LIN .
-40~+85℃	~
SMA-50K	
SMA-50K	. Š.
VFD+Keypad	All Contractions
RS422/LAN port	12
Standard 1U case	1 ¹
10MHz, internal and external clo	ock switching

S Band Downconversion Equipment

S-Band 2-2.8GHz Downconversion Equipment

Input Frequency Output Frequency Gain Gain Step Gain Flatness Third-Order Intermodulation Output P-1 Signal 1dB Bandwidth Noise Figure Frequency Step Interval Frequency Step Interval Frequency Stability Input Signal Level Phase Noise

Harmonic SuppressionSpurious Suppression (max. gain)Medium Freq. SuppressionImage RejectionInput/Output VSWRGroup DelayLO LeakageOperating TemperatureStorage TemperatureInput InterfaceOutput InterfaceLocal ControlRemote ControlDimensionExternal Ref.

2-2.8GHz 70/140/720MHz 30~50dB 0.1dB step controllable ≤1dBp-p ≤-60dBc ≥10dBm ±20/±40±250MHz ≤12dB 10kHz ±5x10-8/day -80~-20dBm ≤-85dBc/Hz@100Hz ≤-100dBc/Hz@1kHz ≤-105dBc/Hz@10kHz ≤-110dBc/Hz@100kHz ≥45dBc ≥60dBc ≥60dBc ≥70dBc <1.5 <2ns Input end is less than -70dBm **-40~+55**℃ **-40~+85**℃ SMA-50K BNC-50K VFD+Keypad RS422/LAN port Standard 1U case 10MHz, internal and external clock switching

S-Band 3.2-4.2GHz Downconversion Equipment

Input Frequency Output Frequency Gain Gain Step Gain Flatness Third-Order Intermodulation Output P-1 Signal 1dB Bandwidth Noise Figure Frequency Step Interval Frequency Step Interval Frequency Stability Input Signal Level Phase Noise

	Harmonic Suppression
Spurious	Suppression (max. gain)
M	edium Freq. Suppression
, Š	Image Rejection
- STEL	Input/Output VSWR
1	Group Delay
	LO Leakage
	Operating Temperature
	Storage Temperature
	Input Interface
	Output Interface
10	Local Control
	Remote Control
-	Dimension
	External Ref.

3.2-4.2GHz 70/140/720MHz 30dB 0.1dB step controllable ≤1dBp-p ≤-60dBc ≥10dBm ±20/±40±250MHz ≤12dB 10kHz ±5x10-8/day -80~-20dBm ≤-85dBc/Hz@100Hz ≤-95dBc/Hz@1kHz ≤-100dBc/Hz@10kHz ≤-105dBc/Hz@100kHz ≥45dBc ≥60dBc ≥60dBc ≥70dBc <1.5 <2ns Input end is less than -70dBm -10~+55℃ **-40~+85**℃ SMA-50K SMA-50K VFD+Keypad RS422/LAN port Standard 1U case

10MHz, internal and external clock switching

X-Band Downconversion Equipment

X-Band 7-9GHz Downconversion Equipment

Input Frequency Output Frequency Gain Gain Step Gain Flatness Third-Order Intermodulation Output P-1 Signal 1dB Bandwidth Noise Figure Frequency Step Interval Frequency Step Interval Frequency Step Interval Phase Noise Harmonic Suppression

 Harmonic Suppression

 Spurious Suppression (max. gain)

 Medium Freq. Suppression

 Image Rejection

 Input/Output VSWR

 Group Delay

 LO Leakage

 Operating Temperature

 Storage Temperature

 Input Interface

 Output Interface

 Local Control

 Remote Control

 Dimension

 External Ref.

7-9GHz 70/140/720/1500MHz 30~50dB 0.1dB step controllable ≤1.5dBp-p ≤-60dBc ≥10dBm ±20/±40/±250/±300/±450MHz ≤13dB 10kHz ±5x10-8/day -80~-20dBm ≤-75dBc/Hz@100Hz ≤-90dBc/Hz@1kHz ≤-95dBc/Hz@10kHz ≤-97dBc/Hz@100kHz ≥45dBc ≥60dBc ≥60dBc ≥70dBc <1.5 <2ns Input end is less than -70dBm **-10~+55**℃ **-40~+85**℃ SMA-50K SMA-50K VFD+Keypad RS422/LAN port Standard 1U case 10MHz, internal and external clock switching

Ku Band Downconversion Equipment

Ku-Band 10.75-12.75GHz Downconversion Equipment

Input Frequency Output Frequency Gain Gain Step Gain Flatness Third-Order Intermodulation Output P-1 Signal 1dB Bandwidth Noise Figure Frequency Step Interval Frequency Step Interval Frequency Step Interval Phase Noise

Harmonic Suppression Spurious Suppression (max. gain) Medium Freq. Suppression Image Rejection Input/Output VSWR Group Delay LO Leakage Operating Temperature Storage Temperature Input Interface Output Interface Local Control Remote Control Dimension External Ref.

10.75-12.75GHz 70/140/720/1200/1500MHz 30~50dB 0.1dB step controllable ≤1.5dBp-p ≤-60dBc ≥10dBm ±20/±40/±250/±300/±450MHz ≤13dB 10kHz ±5x10-8/day -80~-20dBm ≤-75dBc/Hz@100Hz ≤-90dBc/Hz@1kHz ≤-95dBc/Hz@10kHz ≤-97dBc/Hz@100kHz ≥45dBc ≥55dBc ≥60dBc ≥70dBc <1.5 <2ns Input end is less than -70dBm **-10~+55**℃ **-40~+85**℃ SMA-50K SMA-50K VFD+Keypad RS422/LAN port Standard 1U case 10MHz, internal and external clock switching

Ka Band Downconversion Equipment

Ka-Band 25.5-27.5GHz Downconversion Equipment

Input Frequency Output Frequency Gain Gain Step Gain Flatness Third-Order Intermodulation Output P-1 Signal 1dB Bandwidth Noise Figure Frequency Step Interval Frequency Step Interval Frequency Stability Input Signal Level Phase Noise

Harmonic SuppressionSpurious Suppression (max. gain)Medium Freq. SuppressionImage RejectionInput/Output VSWRGroup DelayLO LeakageOperating TemperatureStorage TemperatureInput InterfaceOutput InterfaceLocal ControlRemote ControlDimensionExternal Ref.

25.5-27.5GHz 70/140/720/1200/1500MHz 30~50dB 0.1dB step controllable ≤1.5dBp-p ≤-60dBc ≥10dBm ±20/±40/±250/±300/±450MHz ≤13dB 10kHz ±5x10-8/day -80~-20dBm ≤-75dBc/Hz@100Hz ≤-80dBc/Hz@1kHz ≤-85dBc/Hz@10kHz ≤-95dBc/Hz@100kHz ≥45dBc ≥55dBc ≥60dBc ≥70dBc <1.5 <2ns Input end is less than -70dBm **-10~+55**℃ **-40~+85**℃ SMA-2.92K SMA-50K VFD+Keypad RS422/LAN port Standard 1U case 10MHz, internal and external clock switching

1-18GHz Broadband Downconversion Equipment

1-18GHz Broadband Downconversion Equipment



Input Frequency Output Frequency Gain Gain Step Gain Flatness Third-Order Intermodulation Output P-1 Signal 1dB Bandwidth Noise Figure Frequency Step Interval Frequency Step Interval Input Signal Level

Phase Noise

Spurious Suppression (max. ga	in)
Medium Freq. Suppressi	on
Image Rejecti	on
Input VSV	VR
Output VSV	VR
Group Del	ay
Harmonic Suppressi	on
LO Leaka	ge
Operating Temperatu	ire
Storage Temperatu	ire
Input Interfa	ce
Output Interfa	ce
Local Cont	rol
Remote Cont	rol
Dimensi	on
External R	ef.

1-18GHz 70/140/720/1200/1500MHz 30~50dB 0.1dB step controllable ≤1.5dBp-p ≤-60dBc ≥10dBm ±20/±40/±250/±300/±450MHz ≤13dB 10kHz ±5x10-8/day -70~-35dBm ≤-75dBc/Hz@100Hz ≤-80dBc/Hz@1kHz ≤-85dBc/Hz@10kHz ≤-95dBc/Hz@100kHz ≥60dBc ≥60dBc ≥60dBc ≤2.5 ≤1.5 <5ns ≥50dBc Input end is less than -80dBm **-10~+55**℃ **-40~+85**℃ SMA-2.92K SMA-50K VFD+Keypad RS422/LAN port Standard 1U case 10MHz, internal and external clock switching

18-31GHz Broadband Downconversion Equipment

18-31GHz Broadband Downconversion Equipment(Gain=30dB)



nput Frequency
Output Frequency
Gain
Gain Step
Gain Flatness
Third-Order Intermodulation
Output P-1
Signal 1dB Bandwidth
Noise Figure
Frequency Step Interval
Frequency Stability
Input Signal Level

Phase Noise

18-31GHz	
70/720/1200MHz	
30dB	
0.5dB step controllable	
≤2dBp-p	0
≤15dBc	PIE
≥10dBm	V
±20/±250/±450MHz	
<u>≤12dB</u>	
10kHz	
±5x10-8/day	
-70~-35dBm	
≤-70dBc/Hz@100Hz	

≤-83dBc/Hz@10kHz

Spurious Suppression (max. gain)	Spu
Medium Freq. Suppression	J ^S
Image Rejection	DIFE
Input VSWR	V
Output VSWR	
Group Delay	
LO Leakage	
Operating Temperature	
Storage Temperature	
Input Interface	12
Output Interface	
Local Control	
Remote Control	
Dimension	
External Ref.	

≥60dBc	J ^X
≥60dBc	
≥50dBc	1010
≤2.5	
≤1.5	A REAL
<3ns	12
Input end is less than -70dB	m
-10~+60 ℃	ALC: NO.
-40~+85℃	12
SMA-50K	
SMA-2.92K	LIN .
VFD+Keypad	1212
RS422/LAN port	
Standard 2U case	Left -
10MHz, internal and external	al clock switching

18-31GHz Broadband Downconversion Equipment(Gain=50dB)



Input Frequency Output Frequency Gain Gain Step Gain Flatness Third-Order Intermodulation Output P-1 Signal 1dB Bandwidth Noise Figure Frequency Step Interval Frequency Step Interval Frequency Stability Input Signal Level Phase Noise

Medium Freq. Suppression
Image Rejection
Input VSWR
Output VSWR
Group Delay
Harmonic Suppression
LO Leakage
Operating Temperature
Storage Temperature
Input Interface
Output Interface
Local Control
Remote Control
Dimension
External Ref

1.	
25	
18-31GHz	2
70/720/1200MHz	LE LIT
50dB	10
0.1dB step controllable	.×
≤3dBp-p	E Contra
≤20dBc	
≥10dBm	
±20/±250/±450MHz	, Ch
≤12dB	10TE
10kHz	V
±5x10-8/day	6 H
-70~-35dBm	101
≤-75dBc/Hz@100Hz	
≤-80dBc/Hz@1kHz	
≤-83dBc/Hz@10kHz	
≤-90dBc/Hz@100kHz	
≥60dBc	, A
≥60dBc	STHE ST
≥70dBc	- V
≤2.5	
≤1.5	
<3ns	1
≥50dBc	
Input end is less than -80dBm	<u>, ji</u> th
-10~+60℃	1,01
-40~+85℃	
SMA-2.92K	¢.
SMA-50K	
VFD+Keypad	
RS422/LAN port	, d ^x
Standard 2U case	1916-

10MHz, internal and external clock switching